



Arthur V. Pohm

Distinguished Professor of Electrical Engineering, 1959-90

Arthur V. Pohm co-invented Magnetoresistive Random Access Memory (MRAM), a revolutionary computer memory technology, and he received many patents for inventing different types of magnetic storage elements. As a faculty member at ISU, he developed a program to improve electronics research and education in the ECpE department, resulting in the Affiliate Program in Solid-State Electronics. This program, led by Pohm, established a graduate education and research program in solid-state electronics. Pohm was elected a Fellow of IEEE for his significant contributions in the development of thin magnetic films as computer memory elements, and for his inspired leadership as an effective researcher, teacher, and mentor to young faculty.

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